ABSTRACT OF THE DISCLOSURE

A memory apparatus having a rewritable nonvolatile memory, and a control circuit. The memory apparatus brings logical addresses into correspondence with physical addresses of the nonvolatile memory and retains a piece of number-of-rewrites information for each logical address. The control circuit can perform a replacement process of a piece of memory information on the nonvolatile memory. In the replacement process, a given logical address judged to have a small number of rewrites based on the number-of-rewrites information is replaced so as to correspond to a different physical address and then data is transferred according to the replacement. Even when data of the logical address smaller in the number of rewrites is assigned to the different physical address, the number of rewrites of the region is still grasped as the number of rewrites of the logical address. The data of the logical address is maintained in a condition such that it can be easily targeted for the rewrite by the replacement process even in the place to which the data is transferred. Thus, a memory cell is made less prone to accumulatively suffering disturb owing to rewrite.